

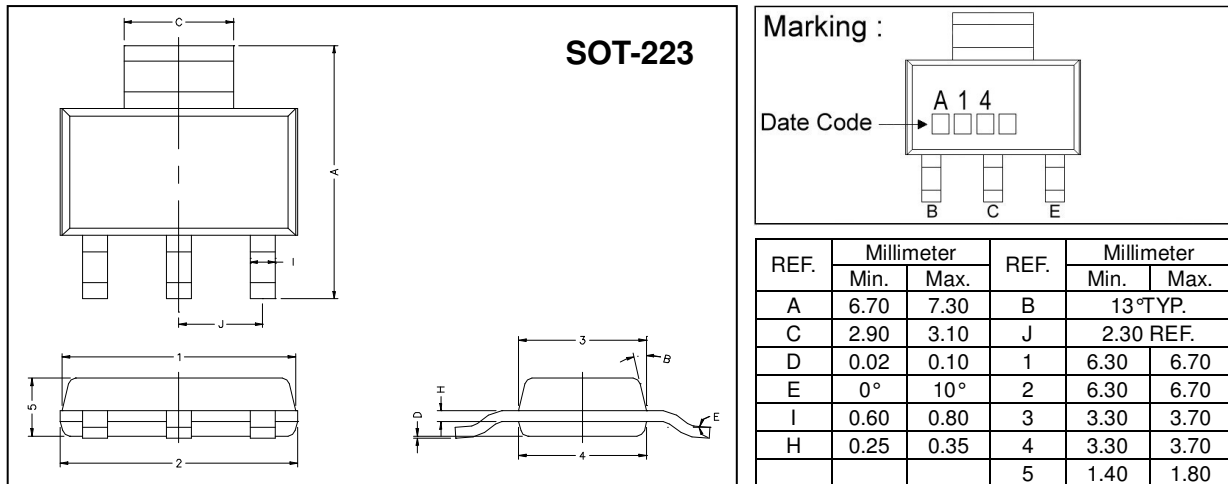
GLA14

NPN EPITAXIAL PLANAR TRANSISTOR

Description

The GLA14 is a Darlington amplifier transistor designed for applications requiring extremely high current gain.

Package Dimensions



Absolute Maximum Ratings at Ta = 25°C

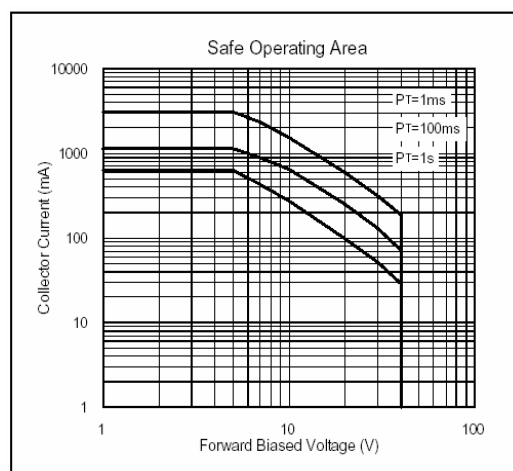
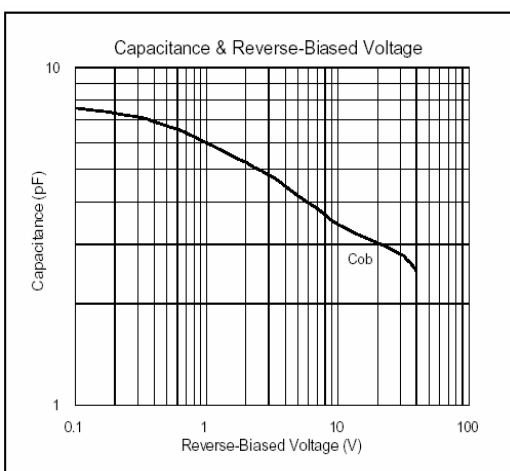
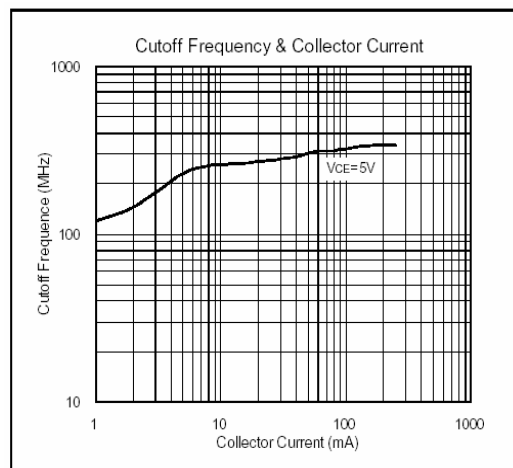
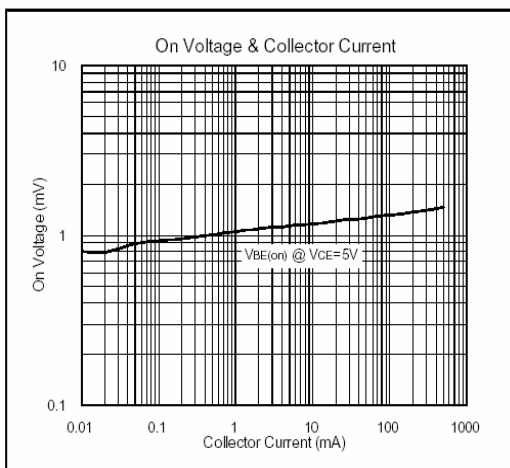
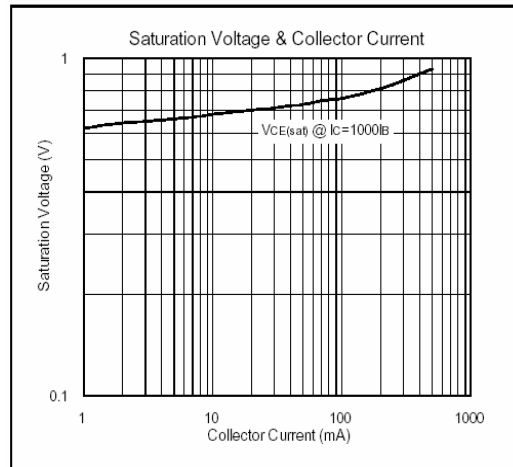
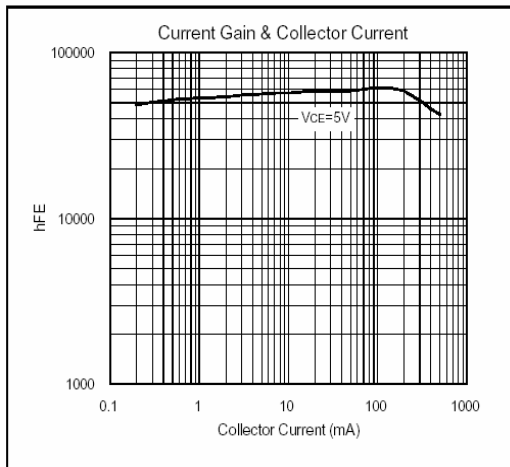
Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	°C
Storage Temperature	Tstg	-55~+150	°C
Collector to Base Voltage	VCBO	30	V
Collector to Emitter Voltage	VCEO	30	V
Emitter to Base Voltage	VEBO	10	V
Collector Current	IC	500	mA
Total Power Dissipation	PD	2	W

Electrical Characteristics (Ta = 25°C unless otherwise noted)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	30	-	-	V	IC=100uA, IE=0
BVCEO	30	-	-	V	IC=100uA, IB=0
BVEBO	10	-	-	V	IE=10uA, IC=0
ICBO	-	-	100	nA	VCB=30V, IE=0
IEBO	-	-	100	nA	VEB=10V, IC=0
*VCE(sat)	-	-	1.5	V	IC=100mA, IB=0.1mA
*VBE(on)	-	-	2.0	V	VCE=5V, IC=100mA
*hFE1	10K	-	-		VCE=5V, IC=10mA
*hFE2	20K	-	-		VCE=5V, IC=100mA
fT	125	-	-	MHz	VCE=5V, IC=10mA, f=100MHz
Cob	-	-	6	pF	VCB=10V, IE=0, f=1MHz

* Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%

Characteristics Curve

**Important Notice:**

- All rights are reserved. Reproduction in whole or in part is prohibited without the prior written approval of GTM.
- GTM reserves the right to make changes to its products without notice.
- GTM semiconductor products are not warranted to be suitable for use in life-support Applications, or systems.
- GTM assumes no liability for any consequence of customer product design, infringement of patents, or application assistance.

Head Office And Factory:

- **Taiwan:** No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- **China:** (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
TEL : 86-21-5895-7671 ~ 4 FAX : 86-21-38950165